

**Remarks/Arguments:**

Applicant thanks Examiner Johnson for his clear explanation of the claim rejections and his response to applicant's argument filed on August 31, 2005. In response to the Office action of October 14, 2005, applicant cancels additional claims 12-31 and inserts new claims 32 and 33. The new claims are fully supported by the original specification and the original drawings. And they distinguish over the cited references:

**Claim 32**

Claim 32 includes a two-layered copper structure with one layer being about 0.6  $\mu\text{m}$  thick. Further, this structure has a nickel layer sandwiched between and contacting both copper layers. This combination is not disclosed or suggested in any of the references.

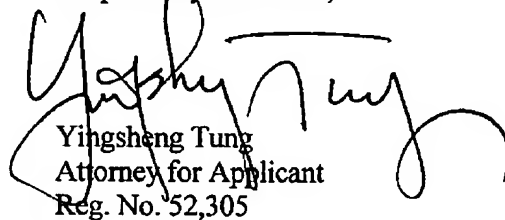
**Claim 33**

Claim 33 properly depends on claim 32 with additional limitation that during a reflow process, the copper in the about 0.6  $\mu\text{m}$  thick layer combines with tin from the solder ball to form a layer of  $\text{Cu}_6\text{Sn}_5$ . This combination is not disclosed in the references as well.

Therefore, applicant respectfully requests further examination of this application and timely allowance of all pending claims.

Texas Instruments Incorporated  
P. O. Box 655474, M/S 3999  
Dallas, Texas 75265  
(972) 917-5355

Respectfully submitted,

  
Yingsheng Tung  
Attorney for Applicant  
Reg. No. 52,305